

Deepak Anandan

List of Publications by Year in descending order

Source: <https://exaly.com/author-pdf/6065489/publications.pdf>

Version: 2024-02-01

19
papers

76
citations

1477746

6
h-index

1473754

9
g-index

19
all docs

19
docs citations

19
times ranked

89
citing authors

#	ARTICLE	IF	CITATIONS
1	Selective Area Epitaxy of Axial Wurtzite -InAs Nanowire on InGaAs NW by MOCVD. , 2021, , .		0
2	Impact of Fringing Field on Shell Radius and Spacer Dielectric on Device Performance of InAs-GaSb Core-Shell Nanowire nFET. ECS Journal of Solid State Science and Technology, 2021, 10, 061004.	0.9	0
3	Effect of Flow Rate Scaling on SAE-InAs Crystal Phase and Integration of Self-Catalyzed InAs/InSb Heterostructure Nanowires on Si (111) Substrate by MOCVD. ECS Journal of Solid State Science and Technology, 2021, 10, 071011.	0.9	0
4	Selective area epitaxy of high quality Wurtzite-InAs heterostructure on InGaAs nanopillars at indium-rich region using MOCVD. Materials Science in Semiconductor Processing, 2021, 135, 106103.	1.9	0
5	Study of Charge Trapping Effects on AlGaIn/GaN HEMTs Under UV Illumination With Pulsed I-V Measurement. IEEE Transactions on Device and Materials Reliability, 2020, 20, 436-441.	1.5	19
6	Low-Frequency Noise Characterization of AlGaIn/GaN HEMTs and MIS-HEMTs under UV Illumination. IEEE Nanotechnology Magazine, 2020, , 1-1.	1.1	7
7	Small signal model and RF performance analysis of InAs/GaSb hetero-junction tunneling field effect transistor. Engineering Research Express, 2020, 2, 035004.	0.8	0
8	Optimization of InAs/GaSb core-shell nanowire structure for improved TFET performance. Materials Science in Semiconductor Processing, 2019, 101, 247-252.	1.9	8
9	Crystal phase control in self-catalyzed InSb nanowires using basic growth parameter V/III ratio. Journal of Crystal Growth, 2019, 522, 30-36.	0.7	7
10	A simple extraction method for parasitic series resistances in GaN HEMTs considering non-quasi-static effects. Microelectronics Journal, 2019, 87, 51-54.	1.1	7
11	Crystal structure control of Au-free InAs and InAs/GaSb heterostructure nanowires grown on Si (111) by metal-organic chemical vapor deposition. Applied Physics Express, 2019, 12, 015502.	1.1	2
12	Growth of foreign-catalyst-free vertical InAs/InSb heterostructure nanowires on Si (111) substrate by MOCVD. Journal of Crystal Growth, 2019, 506, 45-54.	0.7	5
13	Temperature effect on the growth of Au-free InAs and InAs/GaSb heterostructure nanowires on Si substrate by MOCVD. Journal of Crystal Growth, 2018, 490, 19-24.	0.7	7
14	Effect of Two-Step Metal Organic Chemical Vapor Deposition Growth on Quality, Diameter and Density of InAs Nanowires on Si (111) Substrate. Journal of Electronic Materials, 2018, 47, 1071-1079.	1.0	2
15	Growth and Crystal Structure Investigation of InAs/GaSb Heterostructure Nanowires on Si Substrate. IEEE Nanotechnology Magazine, 2018, 17, 1151-1158.	1.1	4
16	Impact of material properties and device architecture on the device performance for a gate all around nanowire tunneling FET. Materials Research Express, 2017, 4, 114002.	0.8	3
17	Growth and crystal structure investigation of self-catalyst InAs/GaSb heterostructure nanowires on Si substrate. , 2017, , .		1
18	Growth of III-V Antimonide Heterostructure Nanowires on Silicon Substrate for Esaki Tunnel Diode. Materials Science Forum, 0, 1055, 1-6.	0.3	1

#	ARTICLE	IF	CITATIONS
19	Improvements of electrical and thermal characteristics for AlGaIn/GaN HEMT grown by metal-organic chemical vapor deposition on silicon-on-insulator (SOI) substrate. Semiconductor Science and Technology, 0, , .	1.0	3